Unit in mm

TOSHIBA Diode Silicon Epitaxial Planar Type

HN1D02FU

Ultra High Speed Switching Application

• HN1D02FU is composed of 2 unit of cathode common.

 $\begin{array}{ll} \bullet & Low \ forward \ voltage & \vdots \ V_{F \ (3)} = 0.90V \ (typ.) \\ \\ \bullet & Fast \ reverse \ recovery \ time \vdots \ t_{rr} = 1.6ns \ (typ.) \end{array}$

Maximum Ratings (Ta = 25°C)

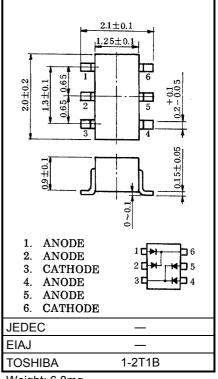
Small total capacitance

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300*	mA
Average forward current	Io	100*	mA
Surge current (10ms)	I _{FSM}	2*	Α
Power dissipation	Р	200	mW
Junction temperature	Тј	125	°C
Storage temperature	T _{stg}	-55~125	°C

 $: C_T = 0.9 pF (typ.)$

*: This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4).

In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.



Weight: 6.8mg

Electrical Characteristics (Q1, Q2, Q3, Q4 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Forward voltage	V _{F (1)}	_	I _F = 1mA	-	0.60	-		
	V _{F (2)}	_	I _F = 10mA	_	0.72	_	٧	
	V _{F (3)}	_	I _F = 100mA	-	0.90	1.20		
Reverse current	I _{R (1)}	_	V _R = 30V	-	_	0.1	μA	
	I _{R (2)}	_	V _R = 80V	-	_	0.5	μΑ	
Total capacitance	C _T	_	V _R = 0, f = 1MHz	_	0.9	3.0	pF	
Reverse recovery time	t _{rr}	_	I _F = 10mA (fig.1)	_	1.6	4.0	ns	

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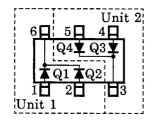
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to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or
damage to property.

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Pin Assignment (Top View)



Marking

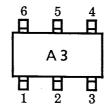
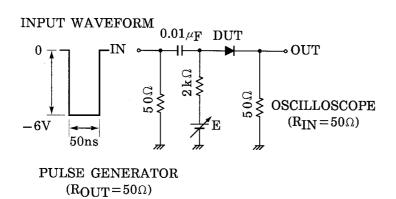
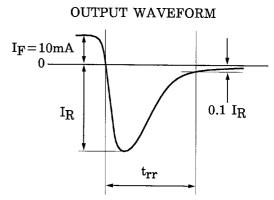
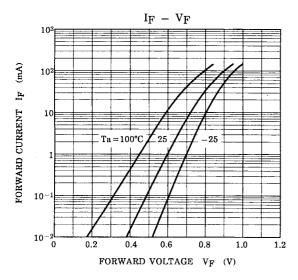


Fig.1 Reverse Recovery Time (trr) Test Circuit

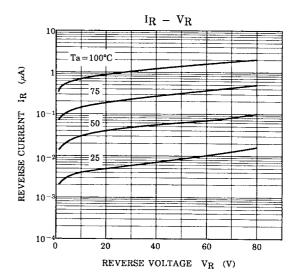




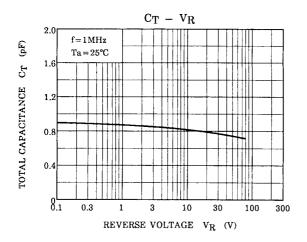
Q1. Q.2. Q3. Q4 Common



Q1. Q.2. Q3. Q4 Common



Q1, Q,2, Q3, Q4 Common



Q1, Q,2, Q3, Q4 Common

